

Silicon PNP Power Transistors

2SA1306 2SA1306A 2SA1306B

DESCRIPTION

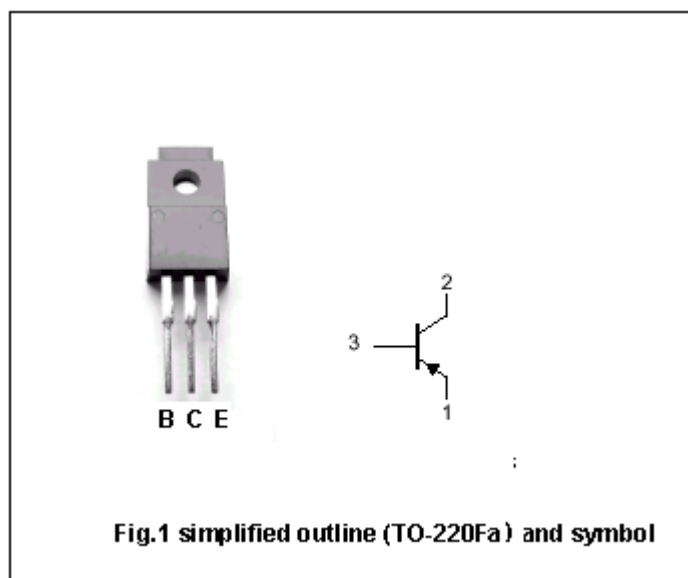
- With TO-220Fa package
- Complement to type
2SC3298, 2SC3298A, 2SC3298B

APPLICATIONS

- Power amplifier applications
- Driver stage amplifier applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector
3	Base

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2SA1306	Open emitter	-160	V
		2SA1306A		-180	
		2SA1306B		-200	
V_{CEO}	Collector-emitter voltage	2SA1306	Open base	-160	V
		2SA1306A		-180	
		2SA1306B		-200	
V_{EBO}	Emitter-base voltage		Open collector	-5	V
I_C	Collector current			-1.5	A
I_B	Base current			-0.15	A
P_C	Collector power dissipation		$T_C=25$	20	W
T_j	Junction temperature			150	
T_{stg}	Storage temperature			-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	2SA1306	I _C =10mA, I _B =0	-160			V
		2SA1306A		-180			
		2SA1306B		-200			
V _{CEsat}	Collector-emitter saturation voltage		I _C =-0.5A, I _B =-50mA			-1.5	V
V _{BE}	Base-emitter voltage		I _C =-0.5A, V _{CE} =-5V			-1.0	V
I _{CBO}	Collector cut-off current		V _{CB} =-160V, I _E =0			-1.0	μA
I _{EBO}	Emitter cut-off current		V _{EB} =-5V, I _C =0			-1.0	μA
h _{FE}	DC current gain		I _C =-0.1A; V _{CE} =-5V	70		240	
C _{ob}	Output capacitance		I _E =0; V _{CB} =-10V, f=1MHz		30		pF
f _T	Transition frequency		I _C =-0.1A; V _{CE} =-10V		100		MHz

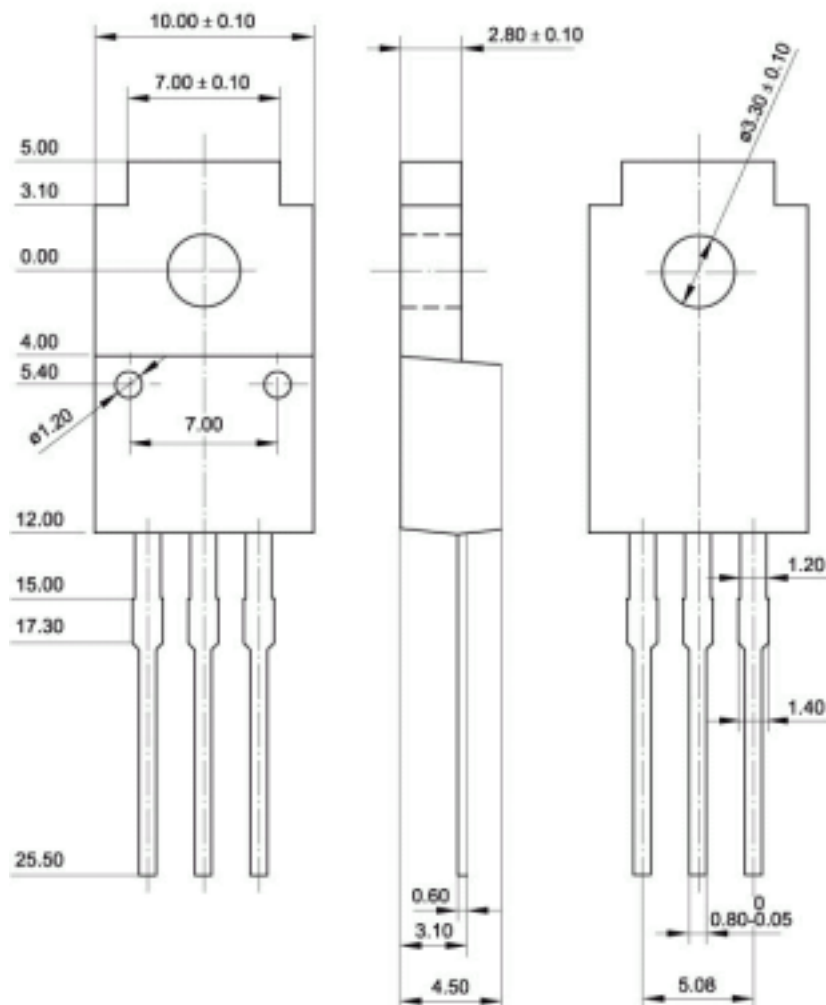
◆ h_{FE} Classifications

O	Y
70-140	120-240

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PACKAGE OUTLINE

Fig.2 Outline dimensions (unindicated tolerance: ± 0.15 mm)